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120 18 1	120 18 1	1	100 5 /	10	120

FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)
 $P_{T(AV)}/P_{F(AV)}(W)$

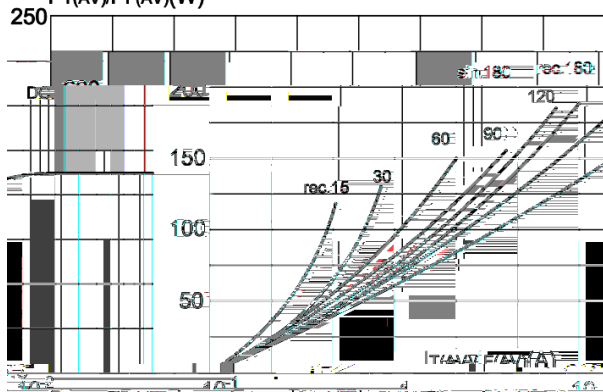


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)
 $R_{th(j-c)}(^{\circ}C/W)$

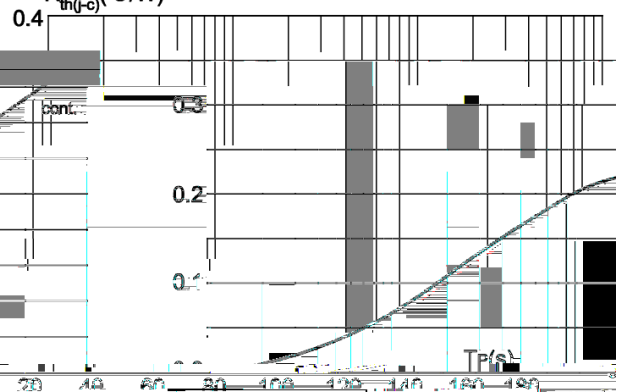


FIG.3: Forward characteristics

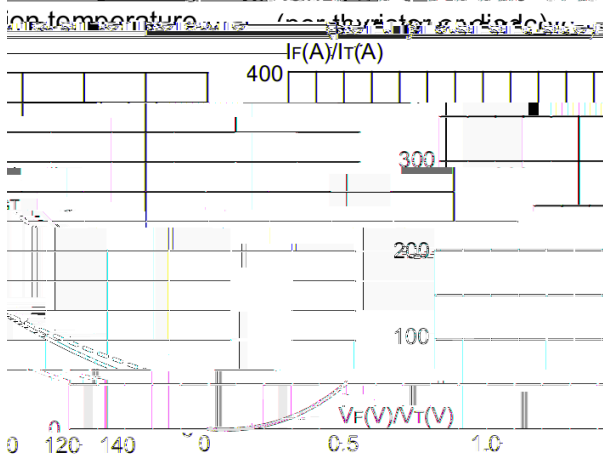


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

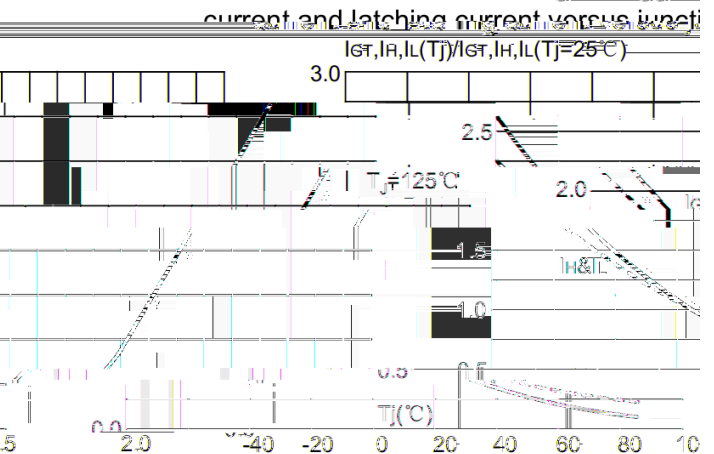


FIG.5: Gate trigger characteristics

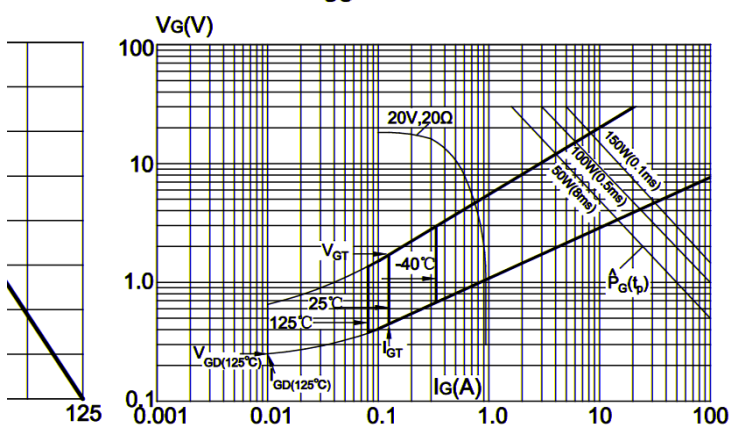


FIG.6: Forward current vs. case temperature
 $I_{F(AV)}(A)$ (per thyristor or diode)

